

1N/FDLL 914/A/B / 916/A/B / 4148 / 4448



Discrete POWER & Signal Technologies

1N/FDLL 914/A/B / 916/A/B / 4148 / 4448



DO-35



LL-34

THE PLACEMENT OF THE EXPANSION GAP HAS NO RELATIONSHIP TO THE LOCATION OF THE CATHODE TERMINAL

COLOR BAND MARKING

DEVICE	1ST BAND	2ND BAND
FDLL914	BLACK	BROWN
FDLL914A	BLACK	GRAY
FDLL914B	BROWN	BLACK
FDLL916	BLACK	RED
FDLL916A	BLACK	WHITE
FDLL916B	BROWN	BROWN
FDLL4148	BLACK	BROWN
FDLL4448	BROWN	BLACK

High Conductance Fast Diode

Sourced from Process D3.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W_{IV}	Working Inverse Voltage	75	V
I_o	Average Rectified Current	200	mA
I_F	DC Forward Current	300	mA
i_f	Recurrent Peak Forward Current	400	mA
$i_{(surge)}$	Peak Forward Surge Current		
	Pulse width = 1.0 second	1.0	A
	Pulse width = 1.0 microsecond	4.0	A
T_{stg}	Storage Temperature Range	-65 to +200	°C
T_J	Operating Junction Temperature	175	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		1N/FDLL 914/A/B / 4148 / 4448	
P_D	Total Device Dissipation Derate above 25°C	500	mW
		3.33	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	°C/W

High Conductance Fast Diode

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Electrical Characteristics

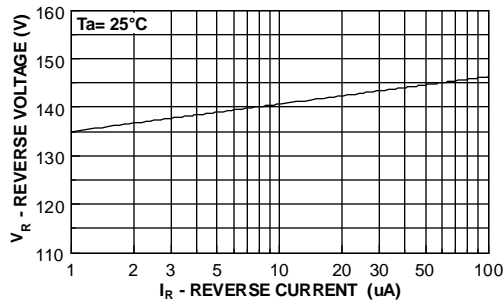
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units	
B _V	Breakdown Voltage	I _R = 100 μA I _R = 5.0 μA	100 75		V V	
I _R	Reverse Current	V _R = 20 V V _R = 20 V, T _A = 150°C V _R = 75 V		25 50 5.0	nA μA μA	
V _F	Forward Voltage	1N914B / 4448 1N916B 1N914 / 916 / 4148 1N914A / 916A 1N916B 1N914B / 4448	I _F = 5.0 mA I _F = 5.0 mA I _F = 10 mA I _F = 20 mA I _F = 30 mA I _F = 100 mA	620 630 720 730 1.0 1.0 1.0	mV mV V V V V	
C _O	Diode Capacitance	1N916/A/B / 4448 1N914/A/B / 4148	V _R = 0, f = 1.0 MHz V _R = 0, f = 1.0 MHz		2.0 4.0	pF pF
T _{RR}	Reverse Recovery Time	I _F = 10 mA, V _R = 6.0 V (60 mA), I _{TR} = 1.0 mA, R _L = 100 Ω		4.0	nS	

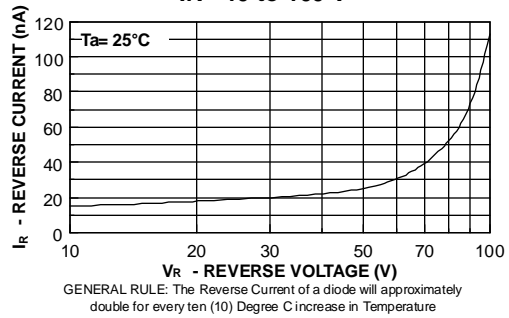
1N/FD/L 914/A/B / 916/A/B / 4148 / 4448

Typical Characteristics

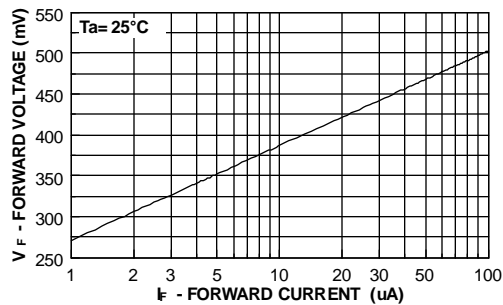
REVERSE VOLTAGE vs REVERSE CURRENT
BV - 1.0 to 100 uA



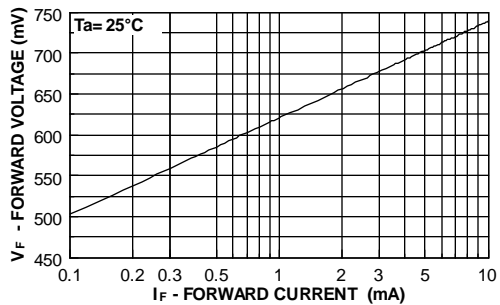
REVERSE CURRENT vs REVERSE VOLTAGE
IR - 10 to 100 V



FORWARD VOLTAGE vs FORWARD CURRENT
VF - 1 to 100 uA



FORWARD VOLTAGE vs FORWARD CURRENT
VF - 0.1 to 100 mA

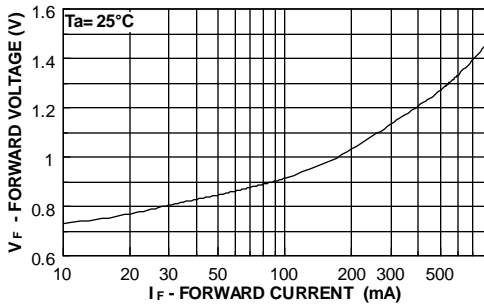


High Conductance Fast Diode

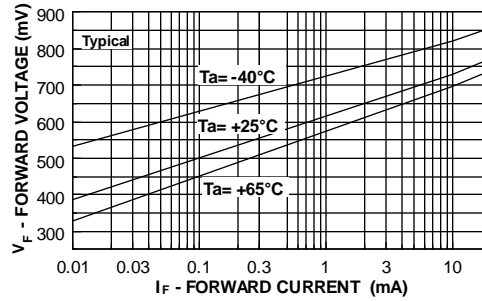
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Typical Characteristics (continued)

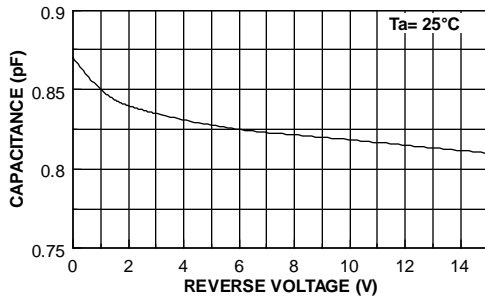
FORWARD VOLTAGE vs FORWARD CURRENT
VF - 10 to 800 mA



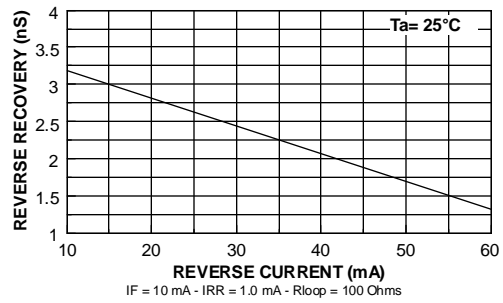
VF - 0.01 - 20 mA (-40 to +65 Deg C)
FORWARD VOLTAGE vs
AMBIENT TEMPERATURE



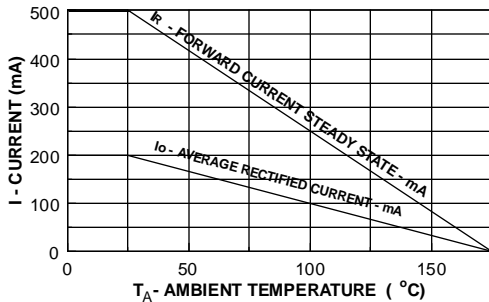
CAPACITANCE vs REVERSE VOLTAGE
VR = 0.0 to 15 V



REVERSE RECOVERY TIME vs
REVERSE CURRENT



Average Rectified Current (Io) &
Forward Current (IF) versus
Ambient Temperature (TA)



POWER DERATING CURVE

